



New Product

DG2001

Vishay Siliconix

Low-Voltage Single SPDT Analog Switch

FEATURES

- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance - r_{ON} : 3 Ω
- Fast Switching - t_{ON} : 20 ns, t_{OFF} : 10 ns
- Low Leakage - I_{COM} : 0.2-nA
- Low Charge Injection - Q_{INJ} : 5 pC
- Low Power Consumption
- TTL/CMOS Compatible
- ESD Protection > 2000 V (Method 3015.7)
- TSOP-6 Package

BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- Sample and Hold Circuits

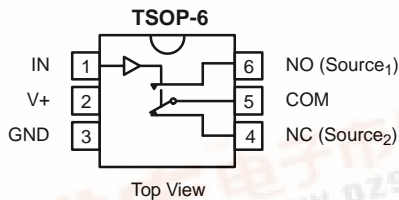
DESCRIPTION

The DG2001 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed, low on-resistance and small physical size, the DG2001 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2001 is built on Vishay Siliconix's low voltage J12 process. The DG2001 has a minimum 2000-V, ESD protection, per Method 3015.7. An epitaxial layer prevents latchup. Break-before-make is guaranteed.

The switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE

Logic	NC	NO
0	ON	OFF
1	OFF	ON

ORDERING INFORMATION

Temp Range	Package	Part Number
-40 to 85°C	TSOP-6	DG2001DV





ABSOLUTE MAXIMUM RATINGS

Reference to GND

V+	-0.3 to +6 V
IN, COM, NC, NO ^a	-0.3 to (V+ + 0.3 V)
Continuous Current (Any terminal)	±50 mA
Peak Current (Pulsed at 1 ms, 10% duty cycle)	±200 mA
ESD (MIL-STD-883B, Method 3015.7)	> 2000 V

Storage Temperature (D Suffix)	-65 to 125°C
Power Dissipation (Packages) ^b	
TSOP-6 ^c	570 mW

Notes:

- Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- All leads welded or soldered to PC Board.
- Derate 7.0 mW/°C above 25°C

SPECIFICATIONS (V+ = 2.0 V)								
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 2.0 V, ±10%, V _{IN} = 0.4 or 1.6 V ^e	Temp ^a	Limits -40 to 85°C			Unit	
				Min ^b	Typ ^c	Max ^b		
Analog Switch								
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V	
On-Resistance	r _{ON}	V+ = 1.8 V, V _{COM} = 1.0 V, I _{NO} , I _{NC} = 10 mA	Room Full		15 17	30 32	Ω	
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 1.8 V, V _{COM} = 0 to V+, I _{NO} , I _{NC} = 10 mA	Room		5			
Switch Off Leakage Current ^g	I _{NO(off)} , I _{NC(off)}	V+ = 2.2 V V _{NO} , V _{NC} = 0.5 V/1.5 V, V _{COM} = 1.5 V/0.5 V	Room Full	-300 -3.5		300 3.5	pA nA	
	I _{COM(off)}		Room Full	-300 -3.5		300 3.5	pA nA	
Channel-On Leakage Current ^g	I _{COM(on)}	V+ = 2.2 V, V _{NO} , V _{NC} = V _{COM} = 0.5 V/1.5 V	Room Full	-350 -3.5		300 3.5	pA nA	
Digital Control								
Input High Voltage	V _{INH}		Full	1.6			V	
Input Low Voltage	V _{INL}		Full			0.4		
Input Capacitance	C _{in}		Full		4		pF	
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	1		1	μA	
Dynamic Characteristics								
Turn-On Time	t _{ON}	V _{NO} or V _{NC} = 1.5 V, R _L = 300 Ω, C _L = 35 pF	Room Full		30	50 53	ns	
Turn-Off Time	t _{OFF}		Room Full		15	30 33		
Break-Before-Make Time	t _d		Room	1	15			
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω	Room		1	10	pC	
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room		-71		dB	
Crosstalk ^d	X _{TALK}		Room		-70			
N _O , N _C Off Capacitance ^d	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		17		pF	
Channel-On Capacitance ^d	C _{ON}		Room		50			
Power Supply								
Power Supply Range	V+	V _{IN} = 0 or V+		1.8		2.20	V	
Power Supply Current	I+				0.01		1.0	μA
Power Consumption	P _C						2.2	μW



SPECIFICATIONS (V+ = 3 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ±10%, VIN = 0.4 or 2.0 V ^e	Temp ^a	Limits -40 to 85°C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA	Room Full		5 6	9.2 10.2	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 2.7 V V _{COM} = 0 to V+, I _{NO} , I _{NC} = 10 mA	Room		3		
Switch Off Leakage Current ^g	I _{NO(off)} , I _{NC(off)}	V+ = 3.3 V, V _{NO} , V _{NC} = 1 V/3 V V _{COM} = 3 V/1 V	Room Full	-400 -4.5		400 4.5	pA nA
	I _{COM(off)}		Room Full	-400 -4.5		400 4.5	pA nA
Channel-On Leakage Current ^g	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 1 V/3 V	Room Full	-450 -4.5		450 4.5	pA nA
Digital Control							
Input High Voltage	V _{INH}		Full	2			V
Input Low Voltage	V _{INL}		Full			0.4	
Input Capacitance	C _{in}		Full		4		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	V _{NO} or V _{NC} = 2.0 V, R _L = 300 Ω, C _L = 35 pF	Room Full		24	45 48	ns
Turn-Off Time	t _{OFF}		Room Full		12	30 33	
Break-Before-Make Time	t _d		Room	1	13		
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω	Room		3	10	pC
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room		-71		dB
Crosstalk ^d	X _{TALK}		Room		-70		
N _O , N _C Off Capacitance ^d	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		17		pF
Channel-On Capacitance ^d	C _{ON}		Room		50		
Power Supply							
Power Supply Range	V+			2.7		3.3	V
Power Supply Current	I+	V _{IN} = 0 or V+			0.01	1.0	μA
Power Consumption	P _C						3.3



SPECIFICATIONS (V+ = 5 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 5 V, ±10%, VIN = 0.8 or 2.4 V ^e	Temp ^a	Limits -40 to 85°C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 4.5 V, V _{COM} = 3 V, I _{NO} , I _{NC} = 10 mA	Room Full		3 4	7.0 8.0	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 4.5 V, V _{COM} = 0 to V+, I _{NO} , I _{NC} = 10 mA	Room		2		
Switch Off Leakage Current ^g	I _{NO(off)} , I _{NC(off)}	V+ = 5.5 V V _{NO} , V _{NC} = 1 V/4.5 V, V _{COM} = 4.5 V/1 V	Room Full	-900 -5.5		900 5.5	pA nA
	I _{COM(off)}		Room Full	-900 -5.5		900 5.5	pA
Channel-On Leakage Current ^g	I _{COM(on)}	V+ = 5.5 V, V _{NO} , V _{NC} = V _{COM} = 1 V/4.5 V	Room Full	-1000 -5.5		1000 5.5	pA nA
Digital Control							
Input High Voltage	V _{INH}		Full	2.4			V
Input Low Voltage	V _{INL}		Full			0.8	
Input Capacitance	C _{in}		Full		4		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	V _{NO} or V _{NC} = 3 V, R _L = 300 Ω, C _L = 35 pF	Room Full		20	37 40	ns
Turn-Off Time	t _{OFF}		Room Full		10	27 30	
Break-Before-Make Time	t _d		Room	1	10		
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω	Room		7	10	pC
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room		-71		dB
Crosstalk ^d	X _{TALK}		Room		-70		
Source-Off Capacitance ^d	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		17		pF
Channel-On Capacitance ^d	C _{ON}		Room		50		
Power Supply							
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	I+	V _{IN} = 0 or V+			0.01	1.0	μA
Power Consumption	P _C						5.5

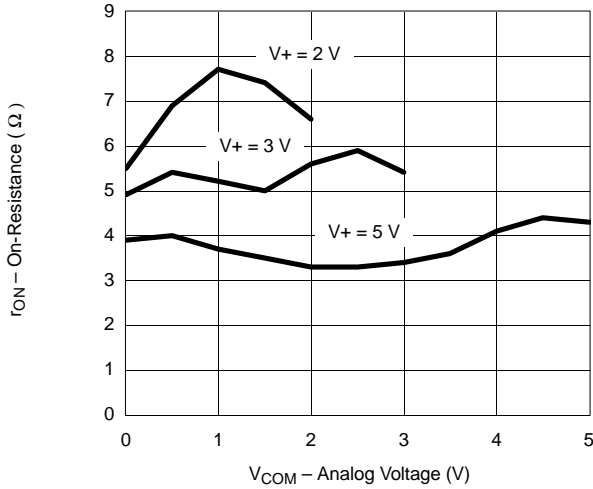
Notes:

- Room = 25°C, Full = as determined by the operating suffix.
- Typical values are for design aid only, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Guarantee by design, nor subjected to production test.
- V_{IN} = input voltage to perform proper function.
- Guaranteed by 5-V leakage testing, not production tested.

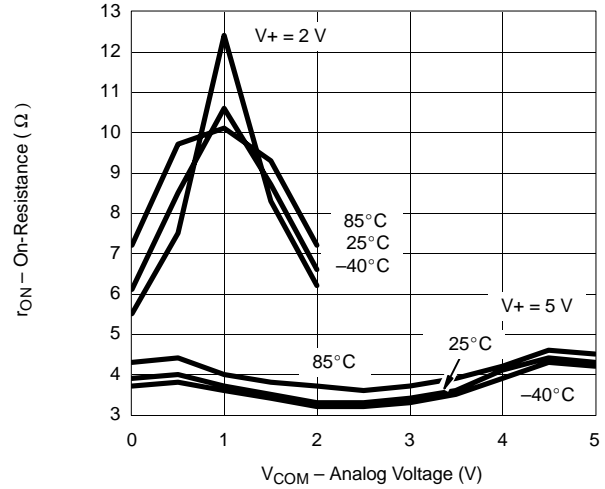


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

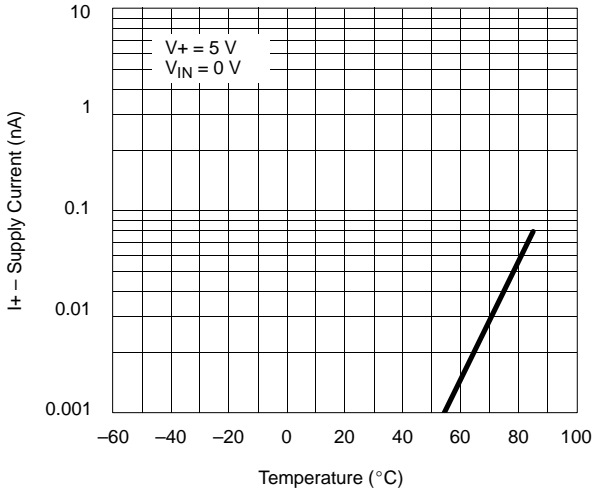
r_{ON} vs. V_{COM} and Supply Voltage



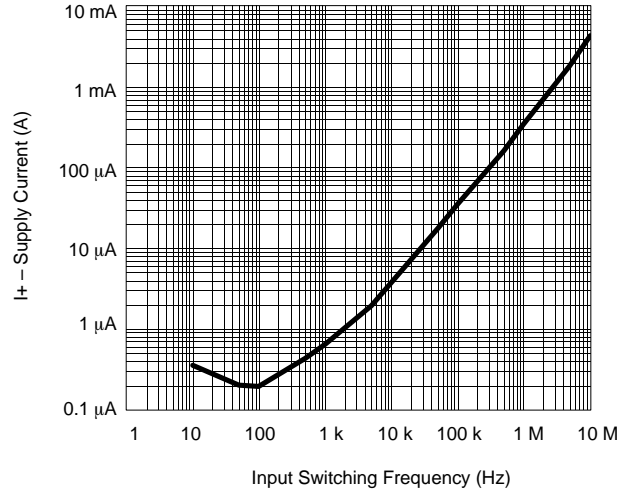
r_{ON} vs. Analog Voltage and Temperature



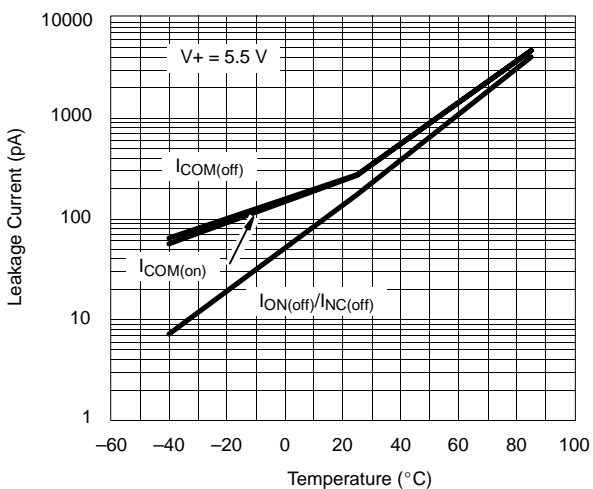
Supply Current vs. Temperature



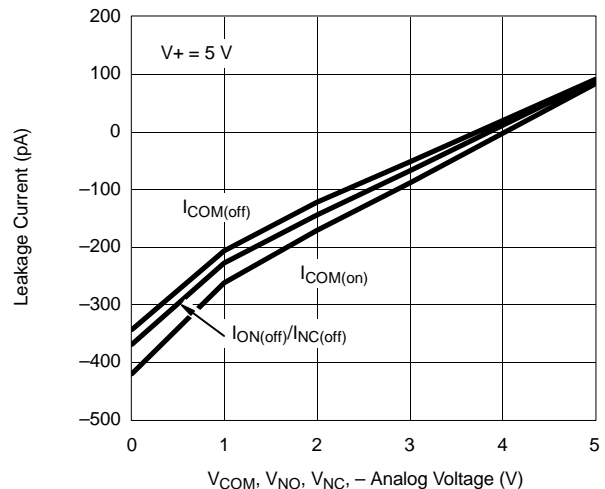
Supply Current vs. Input Switching Frequency



Leakage Current vs. Temperature



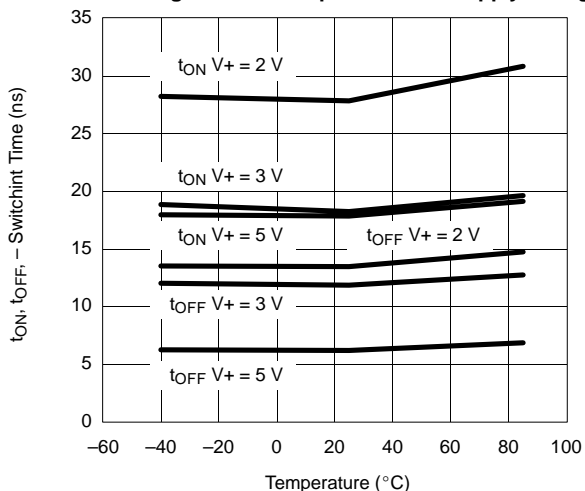
Leakage vs. Analog Voltage



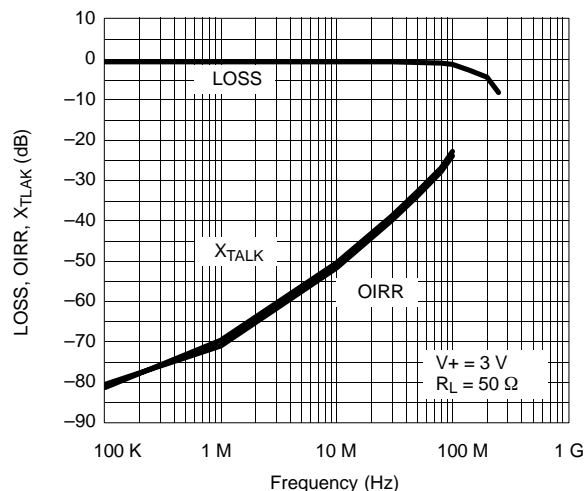


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

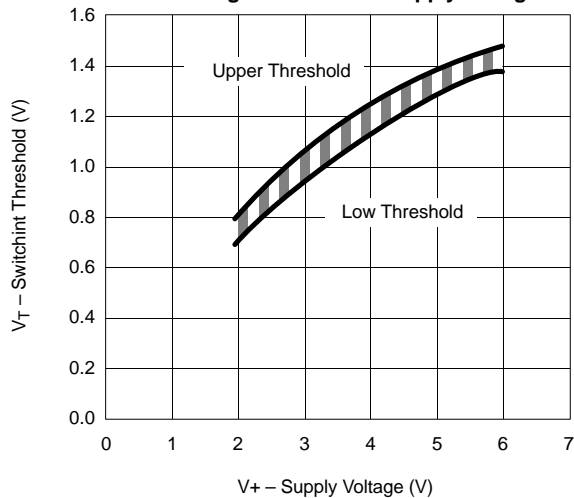
Switching Time vs. Temperature and Supply Voltage



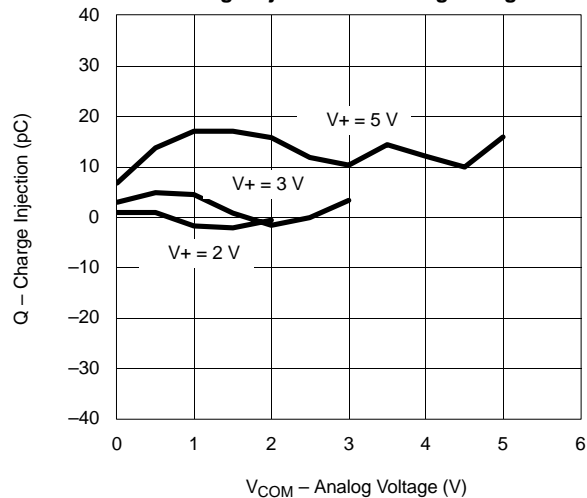
Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



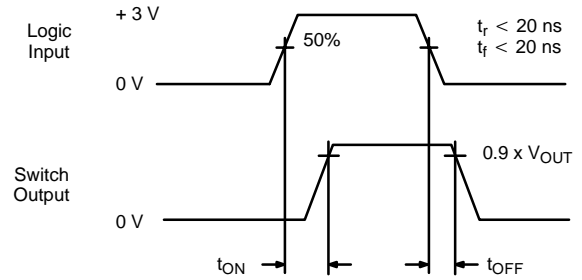
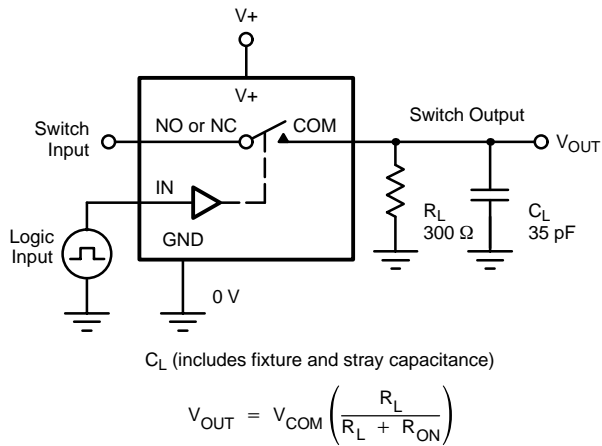
Switching Threshold vs. Supply Voltage



Charge Injection vs. Analog Voltage



TEST CIRCUITS



Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.

FIGURE 1. Switching Time

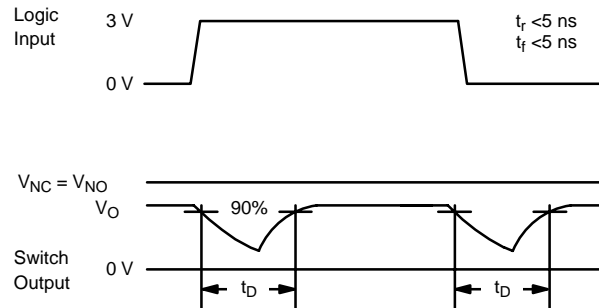
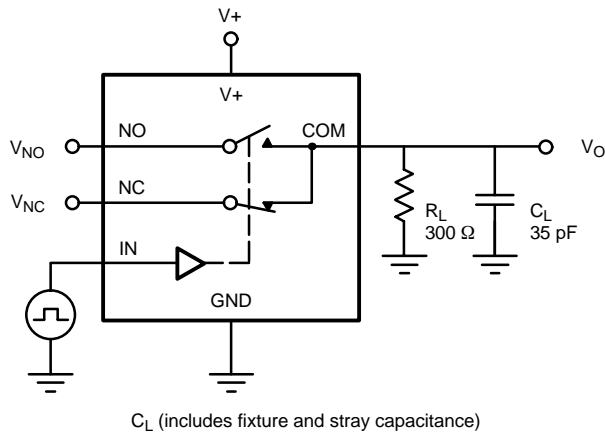
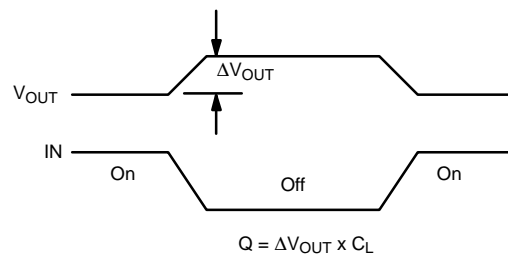
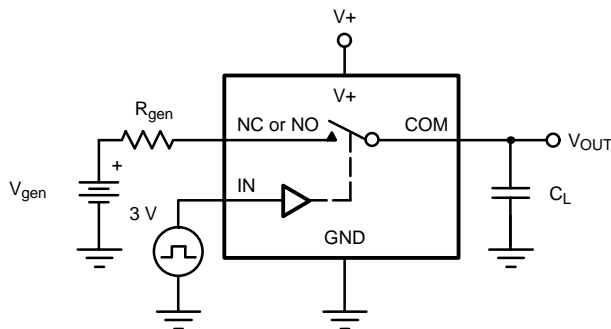


FIGURE 2. Break-Before-Make Interval



IN depends on switch configuration: input polarity determined by sense of switch.

FIGURE 3. Charge Injection

TEST CIRCUITS

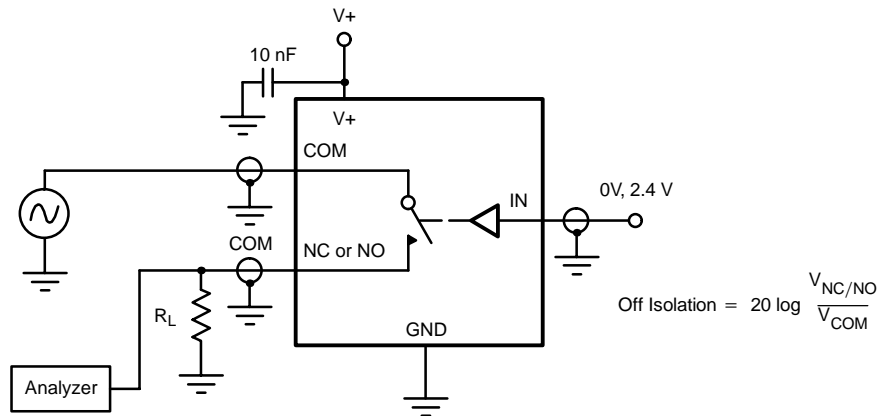


FIGURE 4. Off-Isolation

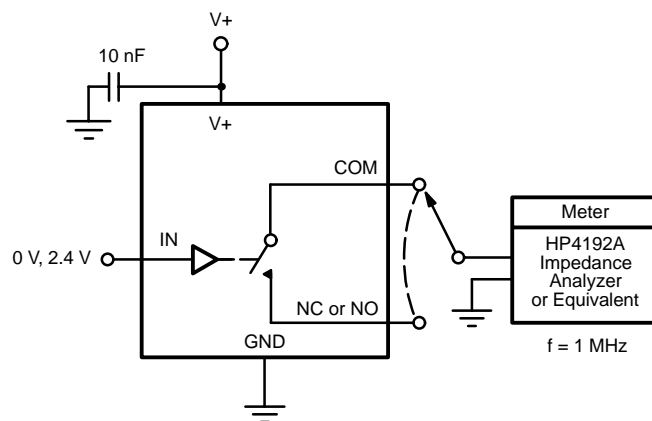


FIGURE 5. Channel Off/On Capacitance